

# Description

The IRLML5203TRPBF uses advanced trench technology

to provide excellent  $R_{DS(ON)}$ , This device is suitable

for use as a load switch or in PWM applications.

### **General Features**

 $V_{DS} = -30V, I_{D} = -4.2A$ 

 $R_{DS(ON)} < 55 m\Omega$  @  $V_{GS}$ =-10V

 $R_{DS(ON)}$  < 75m $\Omega$  @  $V_{GS}$ =-4.5V

## **Application**

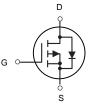
Battery protection

Load switch

Uninterruptible power supply



SOT-23



P-Channel MOSFET

### **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
IRLML5203TRPBF	SOT-23	A19T	3000

### Absolute Maximum Ratings (TA=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
Vos	Drain-Source Voltage	-30	V
Vgs	Gate-Source Voltage	±12	V
I <sub>D</sub>	Drain Current-Continuous	-4.2	А
Івм	Drain Current-Pulsed (Note 1)	-30	А
P <sub>D</sub>	Maximum Power Dissipation	1.2	W
Т,,Тѕтс	Operating Junction and Storage Temperature Range	-55 To 150	${\mathbb C}$
RеJA	Thermal Resistance, Junction-to-Ambient (Note 2)	104	°C/W



## Electrical Characteristics (TA=25°Cunless otherwise noted)

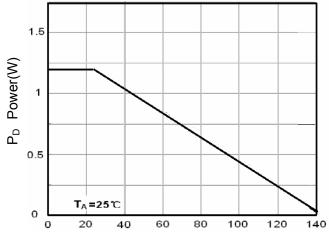
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Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250µA	-30		-	V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-24V,V <sub>GS</sub> =0V	-	-	-1	μΑ
Gate-Body Leakage Current	Igss	V <sub>GS</sub> =±10V,V <sub>DS</sub> =0V	-	-	±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250μA	-0.7	-1	-1.3	V
	RDS(ON)	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4.2A	-	45	55	mΩ
Drain-Source On-State Resistance		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4A	-	56	75	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-1A		72	90	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =-5V,I <sub>D</sub> =-4.2A	-	10	-	S
Input Capacitance	C <sub>lss</sub>		-	880	-	PF
Output Capacitance	Coss	V <sub>DS</sub> =-15V,V <sub>GS</sub> =0V,	-	105	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	65	-	PF
Turn-on Delay Time	td(on)		-	7	-	nS
Turn-on Rise Time	tr	V <sub>DD</sub> =-15V,I <sub>D</sub> =-4.2A V <sub>GS</sub> =-	-	3	-	nS
Turn-Off Delay Time	td(off)	10V,R <sub>GEN</sub> =6Ω	-	30	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	12	-	nS
Total Gate Charge	Qg		-	8.5	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-15V,I <sub>D</sub> =-4.2A,V <sub>GS</sub> =-4.5V	-	1.8	-	nC
Gate-Drain Charge	Q <sub>gd</sub>	- T.OV	-	2.7	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	Vsp	V <sub>GS</sub> =0V,I <sub>S</sub> =-4.2A	-	-	-1.2	V
	L		1	l		

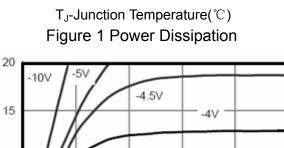
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3、Pulse Test: Pulse Width ≤ 300 $\mu$ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



## **Typical Electrical and Thermal Characteristics**





-3.5V

V<sub>GS</sub>=-3V

4.00

5.00

Vds Drain-Source Voltage (V) Figure 3 Output Characteristics

2.00

3.00

I<sub>D</sub>- Drain Current (A)

10

0.00

1.00

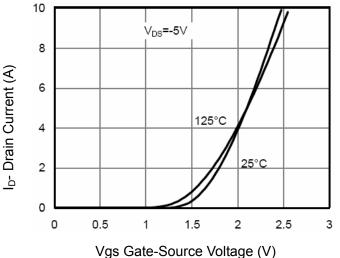
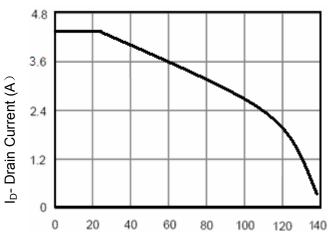
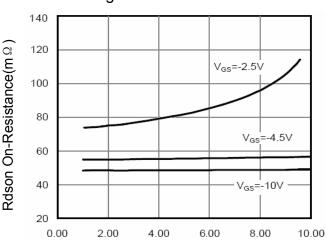


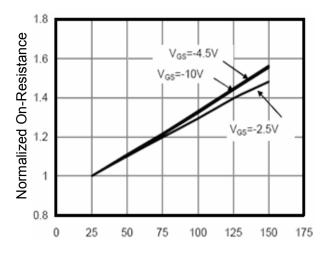
Figure 5 Transfer Characteristics



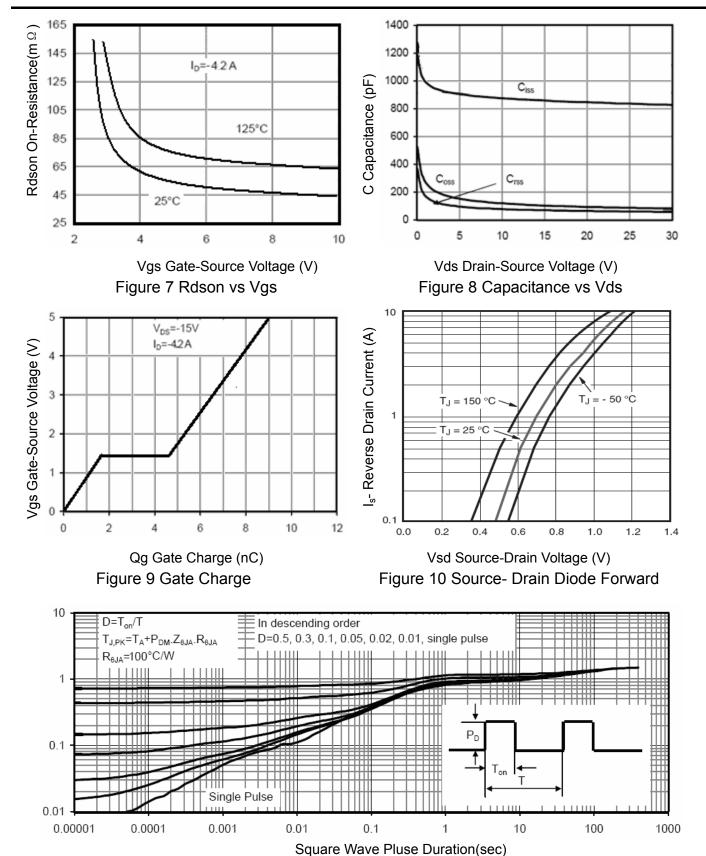
T<sub>J</sub>-Junction Temperature(°C) Figure 2 Drain Current



I<sub>D</sub>- Drain Current (A) Figure 4 Drain-Source On-Resistance



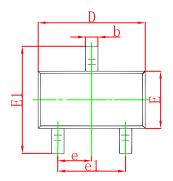
 $\label{eq:TJ-Junction} T_{J}\mbox{-Junction Temperature}({}^{\circ}\!\mathbb{C})$  Figure 6 Drain-Source On-Resistance

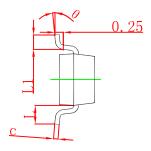


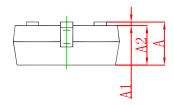
**Figure 14 Normalized Maximum Transient Thermal Impedance** 



# **SOT-23 Package Outline Dimensions**

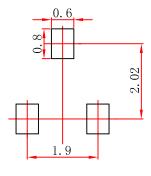






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	TYP	0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **SOT-23 Suggested Pad Layout**



### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.



#### P-Channel Enhancement Mode MOSFET

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